Drain-Source Breakdown Voltage	V_{GS} = 0 V,I_D = 100μA	1200		
Drain-Source Leakage Current	V_{DS} = 1200 V, V_{GS} = 0 V		1	50
Gate Leakage Current	V_{GS} = 22 V, V_{DS} = 0 V			200
Gate Leakage Current	VDS = 0V, VGS= -10V			-200
Gate-Source Threshold Voltage	V_{DS} = V_{GS} , I_D = 10 mA. T_J = 25	2.2	3.2	4.2
	V_{DS} = V_{GS} , I_D = 10 mA. T_J = 175		2.4	
Drain-Source On-State Resistance	V_{GS} = 18V, I_D = 33A T_j = 25 °C		35	40
	V_{GS} = 18V, I_D = 33A T_j = 175 °C		48	
	V_{GS} = 15V, I_D = 33A T_j = 25 °C		38	45
	V_{GS} = 15V, I_D = 33A T_j = 175 °C		52	
Forward transconductance	V_{DS} = 20V I_D = 33A T_j = 25 °C		32	
	V_{DS} = 20V I_D = 33A T_j = 175 °C		27	
Input Capacitance	V_{DS} = 800V,V_{GS} = 0V, V_{AC} = 25mV,T_j = 25 f = 1MHz		2540	
Output Capacitance			97	
Reverse Transfer Capacitance			7	
C_{OSS} Stored Energy			56	
Internal Gate Resistance	f=1MHz V_{AC}=25mV		1.4	
Turn-On Switching Energy	V_{DS} = 800V, I_D = 33A V_{GS} = -5V/18V, $R_{G(ext)}$ = 5.1Ω		155	
Turn-Off Switching Energy			123	
Total Switching Energy			278	
Turn-on Delay Time(				

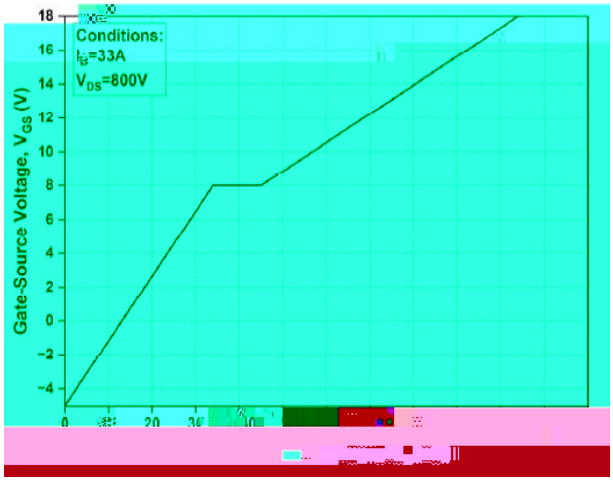


Figure 7. Gate Charge Characteristic

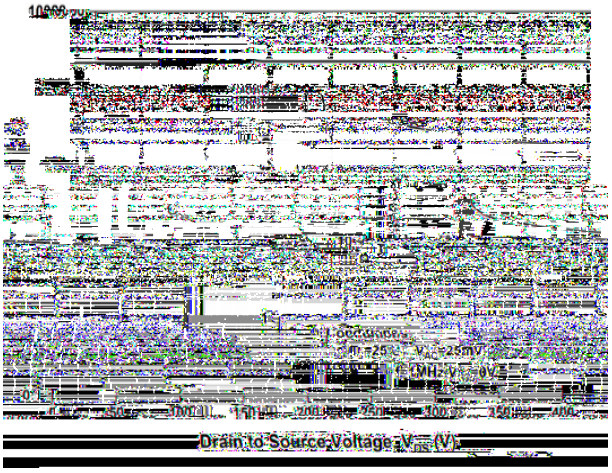


Figure 8. Capacitance vs Drain to Source Voltage (0-400V)

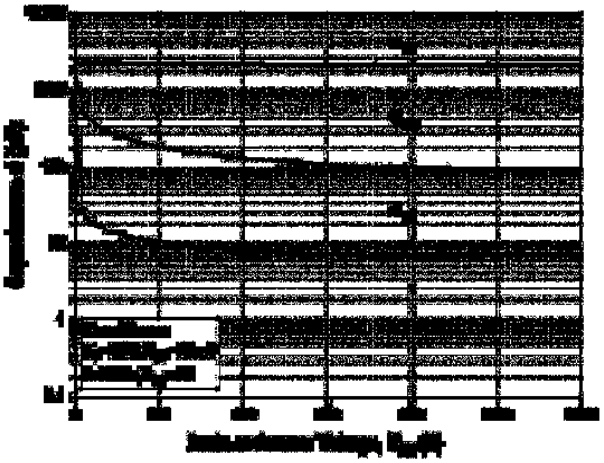


Figure 9. Capacitance vs Drain to Source Voltage (0-1200V)

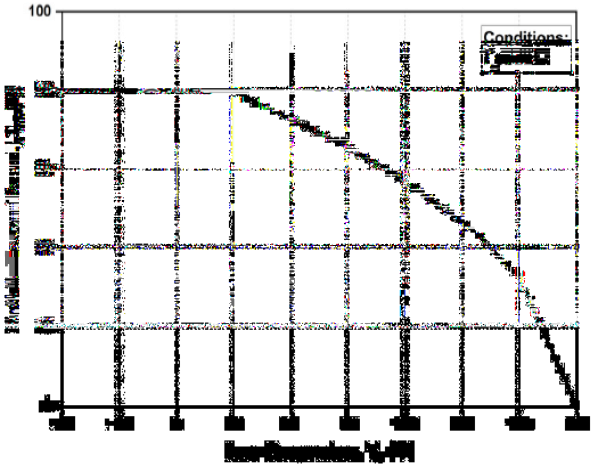


Figure 10. Continuous Drain Current Derating vs. Case Temperature

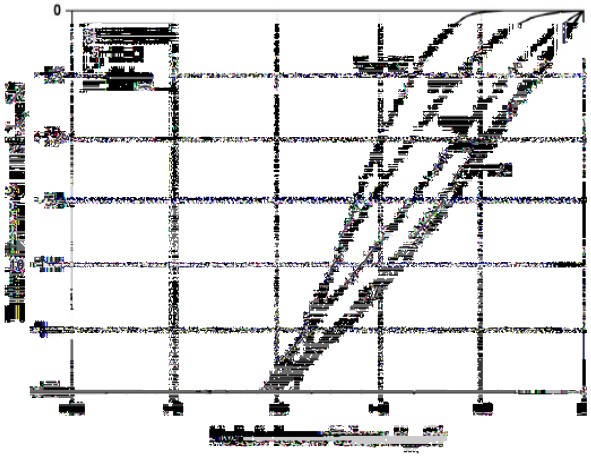


Figure 11. 3rd Quadrant Characteristic at 25

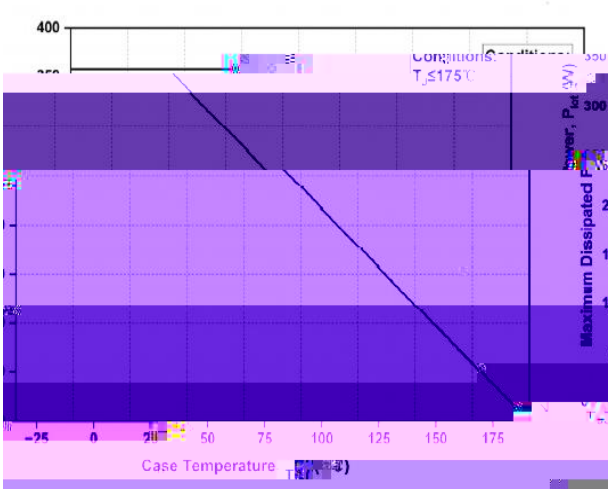


Figure 12. Power Derating

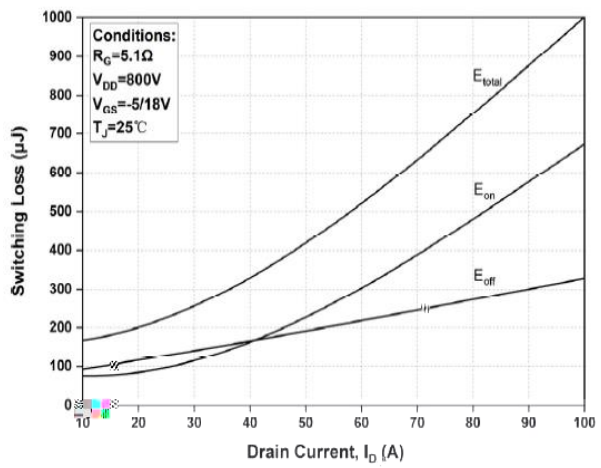


Figure 13. Switching Energy vs. Drain Current

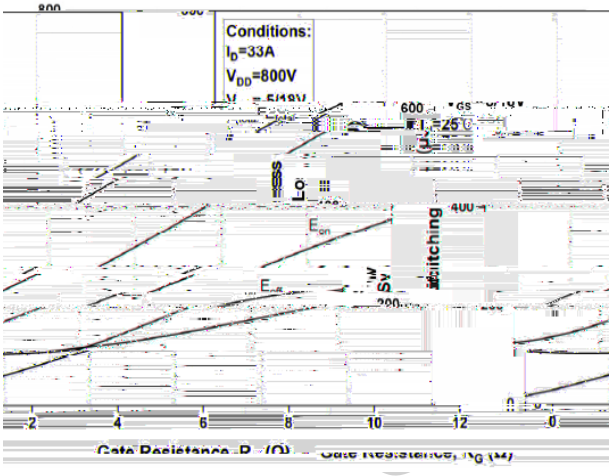


Figure 14. Switching Energy vs. RG(ext)

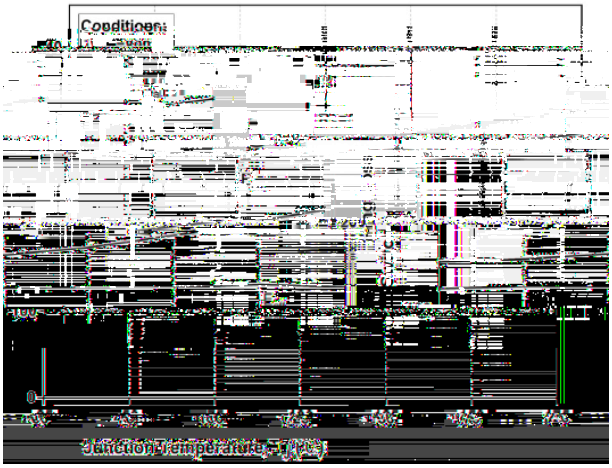


Figure 15. Switching Energy vs. Temperature

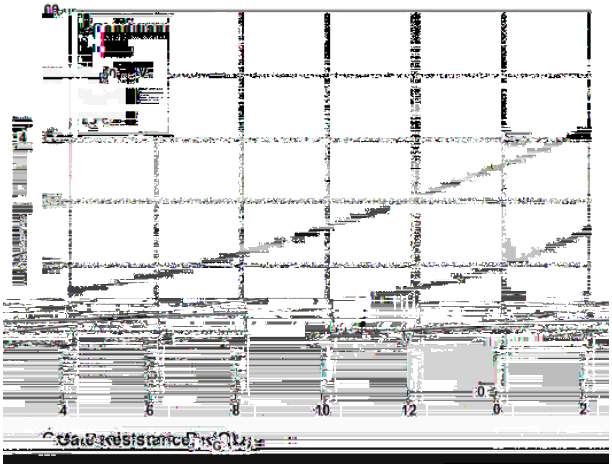


Figure 16. Switching Times vs. RG(ext)

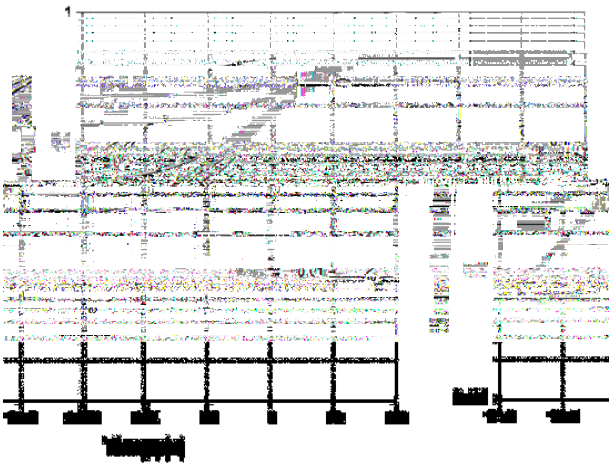


Figure 17. Transient Thermal Impedance

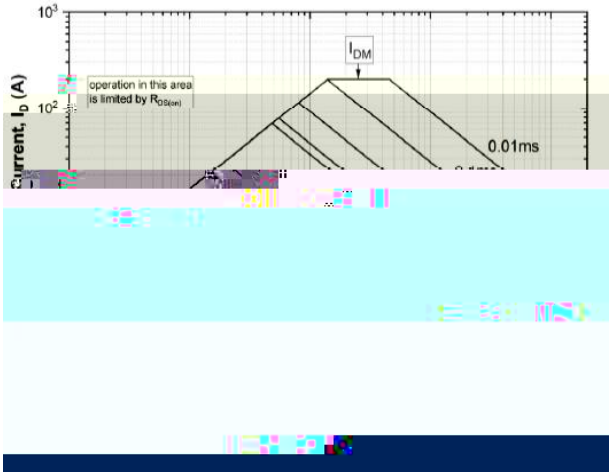
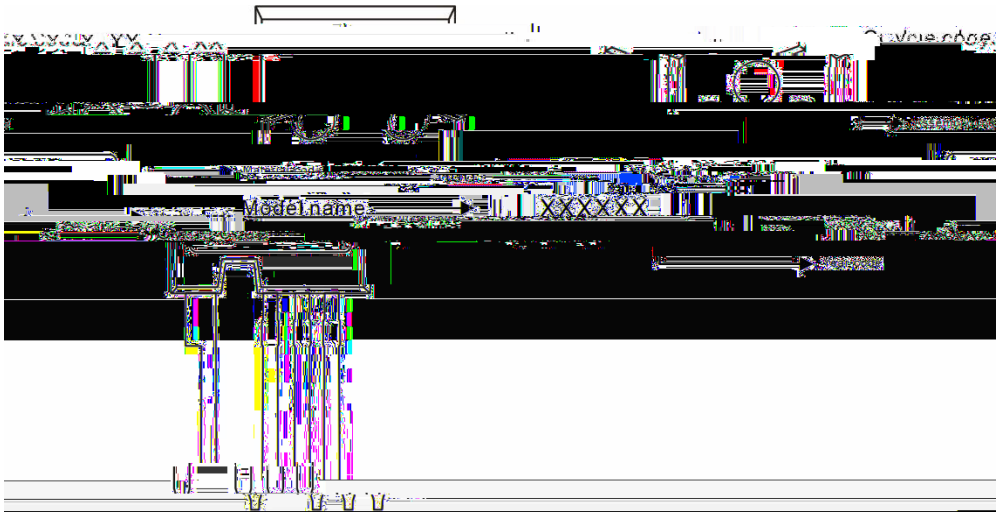


Figure 18. Safe Operating Area



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